Amendments to the Claims

Claims 1-7 (cancelled).

8. (Previously presented) The method of claim 16 wherein the etching comprises plasma etching.

9. (Previously presented) The method of claim 16 wherein the etching comprises magnetically enhanced plasma etching.

10. (Previously presented) The method of claim 16 wherein the etching comprises substantially anisotropic etching of the silicon nitride comprising layer.

Claims 11-13 (Cancelled).

14. (Previously presented) The method of claim 16 wherein the etching chemistry comprises at least two fluorocarbons.

15. (Previously presented) The method of claim 16 wherein the etching chemistry comprises at least three fluorocarbons.

16. (Previously presented) A method of forming integrated circuitry comprising:

forming a layer comprising silicon nitride over a semiconductor substrate;

forming a patterned photoresist comprising masking layer over the silicon nitride layer, the patterned masking layer comprising mask openings therethrough; and

etching the silicon nitride comprising layer through the mask openings substantially selectively to the photoresist comprising layer using an etching chemistry having reactive components consisting of ammonia and at least one fluorocarbon selected from the group consisting of CF_4, C_4F_6, C_4F_8, C_2F_6, C_3F_8, C_5F_8, and chlorofluorocarbons, under etching conditions effective to substantially anisotropically etch the silicon nitride comprising layer, the etching chemistry comprising a volumetric ratio of all fluorocarbon to the ammonia of from 40:1 to 20:1 and providing increased selectivity to the photoresist comprising masking layer than would otherwise occur using identical etching chemistry and identical etching conditions without any ammonia.

Claims 17-19 (Cancelled).

20. (Currently amended) A method of forming integrated circuitry comprising:

forming a layer comprising silicon nitride over a semiconductor substrate;

forming a patterned photoresist comprising masking layer over the silicon nitride layer, the patterned masking layer comprising mask openings therethrough; and

etching the silicon nitride comprising layer through the mask openings substantially selectively to the photoresist comprising layer using an etching chemistry having reactive components consisting of ammonia and at least one of C_4F_6 and C_5F_8, ~~fluorocarbon~~ under etching conditions effective to substantially anisotropically etch the silicon nitride comprising layer, the etching chemistry comprising a volumetric ratio of all fluorocarbon to the ammonia of from 40:1 to 20:1 and providing increased selectivity to the photoresist comprising masking layer than would otherwise occur using identical etching chemistry and identical etching conditions without any ammonia, ~~wherein the fluorocarbon is at least one member selected from the group consisting of C_4F_6 and C_5F_8~~.

21. (Original) The method of claim 16 wherein the silicon nitride comprising layer consists essentially of silicon nitride.

Claims 22-46 (Cancelled).

47. (Previously presented) The method of claim 16 wherein the photoresist comprises 193 nanometer photoresist.

48. (Previously presented) The method of claim 16 comprising introducing the ammonia and fluorocarbon successively into a reaction chamber in which the substrate is received during the etching.

49. (Previously presented) The method of claim 16 wherein the integrated circuitry forming comprises forming shallow trench isolation within the semiconductor substrate, the photoresist comprising masking layer being patterned effective to form a plurality of shallow trench mask openings therethrough.

50. (Previously presented) The method of claim 16 wherein the integrated circuitry forming comprises forming shallow trench isolation within the semiconductor substrate, the silicon nitride comprising layer being formed over a bulk semiconductor substrate, and the photoresist comprising masking layer being patterned effective to form a plurality of shallow trench mask openings therethrough.

51. (Previously presented) The method of claim 20 wherein the fluorocarbon comprises C_4F_6.

52. (Previously presented) The method of claim 20 wherein the fluorocarbon comprises C_5F_8.

53. (Cancelled).

54. (Previously presented) The method of claim 20 wherein the photoresist comprises 193 nanometer photoresist.

55. (Previously presented) The method of claim 20 comprising introducing the ammonia and fluorocarbon successively into a reaction chamber in which the substrate is received during the etching.

56. (Cancelled).

57. (Previously presented) The method of claim 20 wherein the etching comprises plasma etching.

58. (Previously presented) The method of claim 20 wherein the etching comprises magnetically enhanced plasma etching.

59. (Previously presented) The method of claim 20 wherein the etching comprises substantially anisotropic etching of the silicon nitride comprising layer.

60. (Currently amended) The method of claim 20 wherein the etching chemistry comprises both C_4F_6 and C_5F_8 ~~at least two fluorocarbons~~.

Claims 61-62. (Cancelled).

63. (Previously presented) The method of claim 20 wherein the integrated circuitry forming comprises forming shallow trench isolation within the semiconductor substrate, the photoresist comprising masking layer being patterned effective to form a plurality of shallow trench mask openings therethrough.

64. (Previously presented) The method of claim 20 wherein the integrated circuitry forming comprises forming shallow trench isolation within the semiconductor substrate, the silicon nitride comprising layer being formed over a bulk semiconductor substrate, and the photoresist comprising masking layer being patterned effective to form a plurality of shallow trench mask openings therethrough.

65. (New) A method of forming integrated circuitry comprising:

forming a layer comprising silicon nitride over a semiconductor substrate;

forming a patterned photoresist over the silicon nitride layer, the patterned photoresist comprising mask openings therethrough; and

etching the silicon nitride comprising layer through the mask openings using etch chemistry components comprising ammonia and at least one fluorocarbon selected from the group consisting of CF_4, C_4F_6, C_4F_8, C_2F_6, C_3F_8, and chlorofluorocarbons, under etching conditions effective to substantially anisotropically etch the silicon nitride comprising layer.

66. (New) The method of claim 1 wherein the etch chemistry has a volumetric ratio of all fluorocarbon to the ammonia of from 40:1 to 2:1.